

Micron Technology's DDR3 Memory for High-End Computing is Validated with INTEL Platforms

May 14, 2007 at 12:00 AM EDT

Boise, Idaho, Monday, May 14, 2007 – Micron Technology, Inc. today announced that its 1 gigabit (Gb) double data rate (DDR)3 memory components for high-end computing applications have been successfully validated with Intel desktop platforms.

Ideal for data-intensive computing applications from PC gaming to super computing, Micron's 1 Gb DDR3 products provide the lowest cost-per-bit solution available on Micron's 78nm 6F2 process, have a smaller die size premium over DDR2 compared with 512 megabit (Mb) products, offer lower power on modules that can utilize either 512Mb or 1Gb and meet the minimum system density requirements of 1 gigabyte.

"Micron's strength in advanced DRAM technology has given us the industry leading position in high density memory solutions, and we're pleased our DDR3 memory technology is successfully operating on Intel desktop platforms," said Brian Shirley, vice president of Micron's memory group.

"Micron's DDR3 memory technology is the next step in the evolution of DDR (Double Data Rate) SDRAM memory technology," said Pete MacWilliams, Senior Fellow, Intel Corporation. "DDR3 memory technology provides increased bandwidth, lower power and better signal integrity to support Intel's platforms in 2007 and beyond."

Additionally, Micron's DDR3 products support data rates of 800 megatransfers per second (MT/s) to 1,066 MT/s with clock frequencies of 400 megahertz (MHz) to 533 MHz respectively, doubling the speed from DDR2. The DDR3 supply voltage has been reduced from 1.8V to 1.5V, reducing power consumption by up to 30 percent.

Evaluation samples of Micron's 1Gb DDR3 components are available to select customers with production expected to begin early next year. Micron's 1Gb DDR3 components will be available in various output configurations (x4, x8 and x16), and will be fully compliant to the most recent JEDEC DDR3 specifications (JEDEC is the leading developer of standards for the semiconductor industry). These components will support module densities from 512 megabytes (MB) through 4 gigabytes (GB) and a variety of module types including UDIMMs, SODIMMs, and RDIMMs.

A 2Gb DDR3 device is also expected to be available from Micron early next year, helping to enable even higher density applications.

About Micron

Micron Technology, Inc., is one of the world's leading providers of advanced semiconductor solutions. Through its worldwide operations, Micron manufactures and markets DRAMs, NAND flash memory, CMOS image sensors, other semiconductor components, and memory modules for use in leading-edge computing, consumer, networking, and mobile products. Micron's common stock is traded on the New York Stock Exchange (NYSE) under the MU symbol. To learn more about Micron Technology, Inc., visit www.micron.com.

Micron and the Micron orbit logo are trademarks of Micron Technology, Inc.

This press release contains forward-looking statements regarding the production of DDR3 memory. Actual events or results may differ materially from those contained in the forward-looking statements. Please refer to the documents the Company files on a consolidated basis from time to time with the Securities and Exchange Commission, specifically the Company's most recent Form 10-K and Form 10-Q. These documents contain and identify important factors that could cause the actual results for the Company on a consolidated basis to differ materially from those contained in our forward-looking statements (see Certain Factors). Although we believe that the expectations reflected in the forward-looking statements are reasonable, we cannot guarantee future results, levels of activity, performance or achievements. We are under no duty to update any of the forward-looking statements after the date of this press release to conform to actual results.

Related Links

Micron Media Center

Contacts

Kirstin Bordner Micron Technology, Inc. +1 (208) 599-0184/mobile +1 (208) 368-5487/direct kbordner@micron.com